

Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

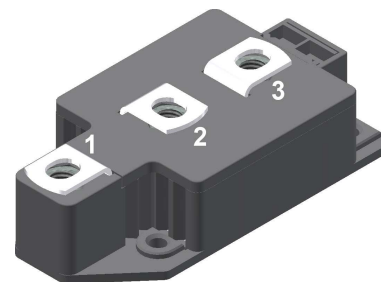
$$I_{FAV} = 300 \text{ A}$$

$$V_F = 1 \text{ V}$$

Phase leg

Part number

MDD310-12N1



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y2

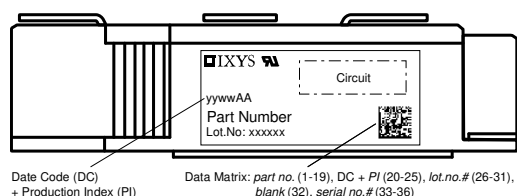
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			20	mA
V_F	forward voltage drop	$I_F = 300\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.13	V
		$I_F = 600\text{ A}$				1.33	V
		$I_F = 300\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.00	V
		$I_F = 600\text{ A}$				1.29	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			300	A
$I_{F(RMS)}$	RMS forward current	180° sine				480	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.75	V
r_F	slope resistance					0.63	mΩ
R_{thJC}	thermal resistance junction to case					0.13	K/W
R_{thCH}	thermal resistance case to heatsink				0.04		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			960	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			11.5	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			12.4	kA
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			9.78	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			10.6	kA
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			661.3	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			641.7	kA ² s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			477.8	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			463.5	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		381		pF

Package Y2			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				254		g
M_D	mounting torque		2.5		5	Nm
M_T	terminal torque		12		15	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0			mm
$d_{Spb/Apb}$		terminal to backside	13.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD310-12N1	MDD310-12N1	Box	2	429155

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

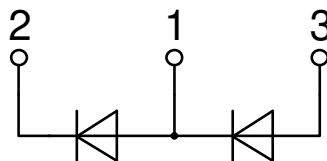
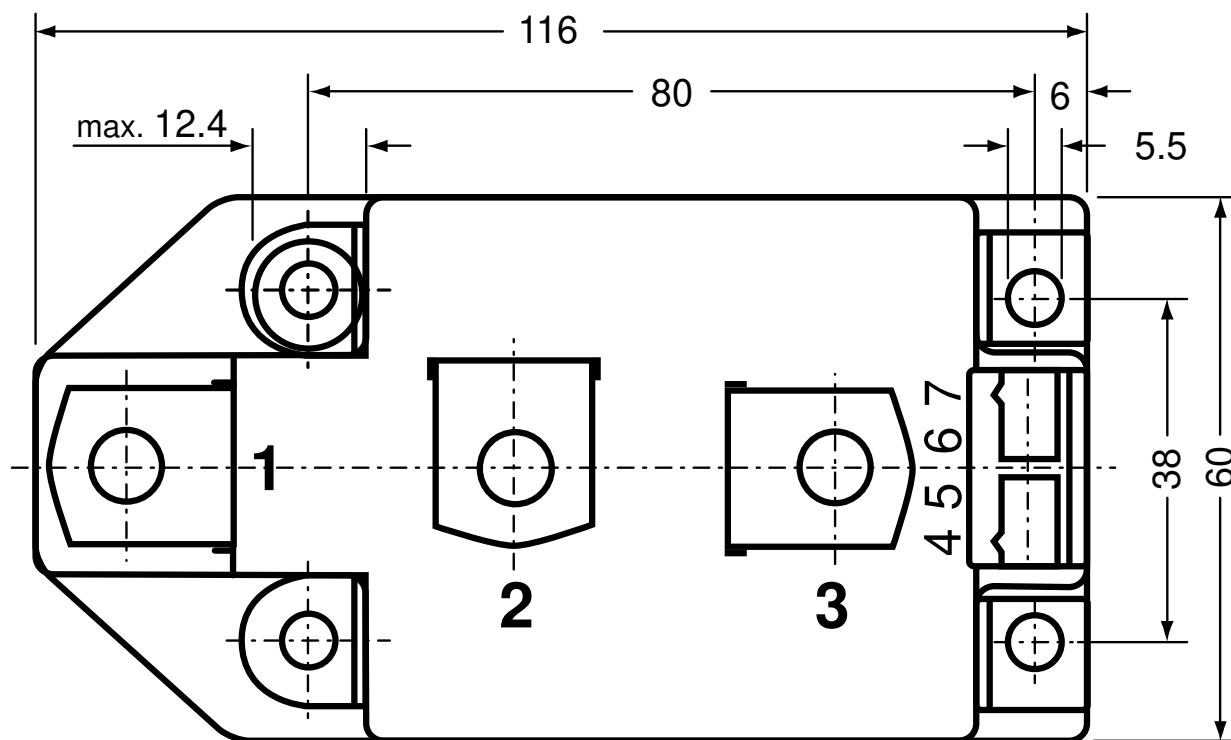
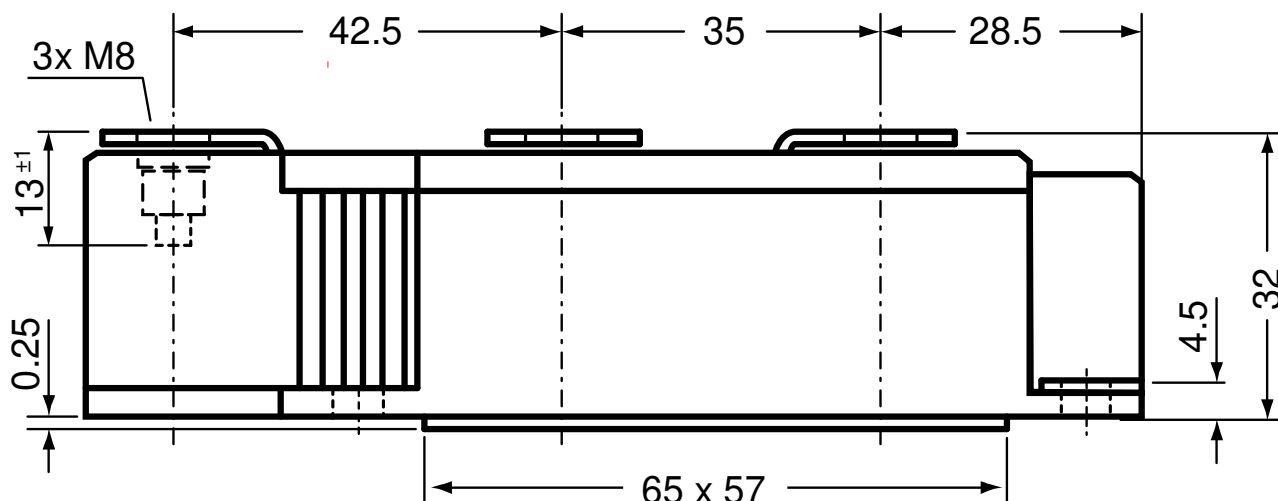
$V_{0\max}$ threshold voltage 0.75

V

$R_{0\max}$ slope resistance * 0.4

mΩ

Outlines Y2



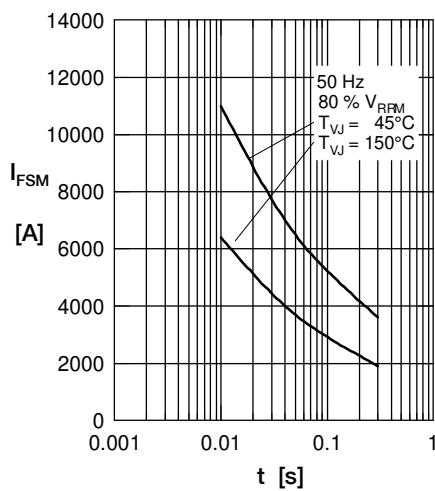
Rectifier


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

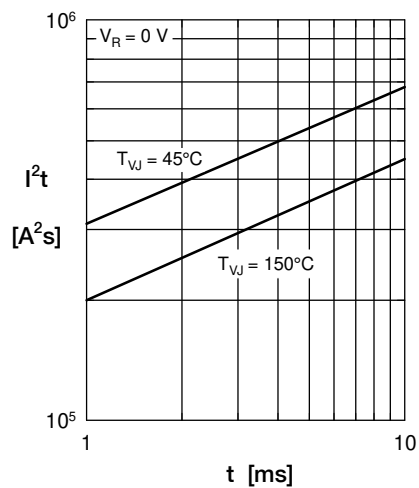


Fig. 2 I^2t versus time (1-10 ms)

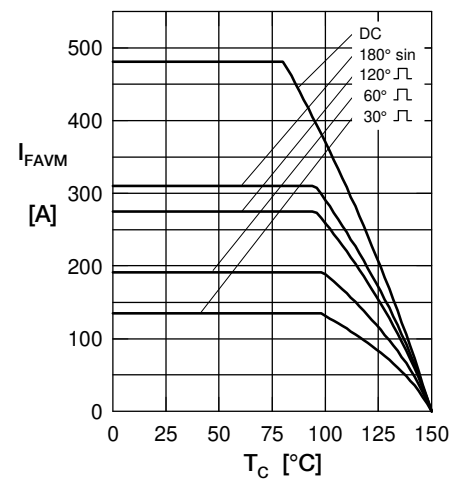


Fig. 3 Maximum forward current at case temperature

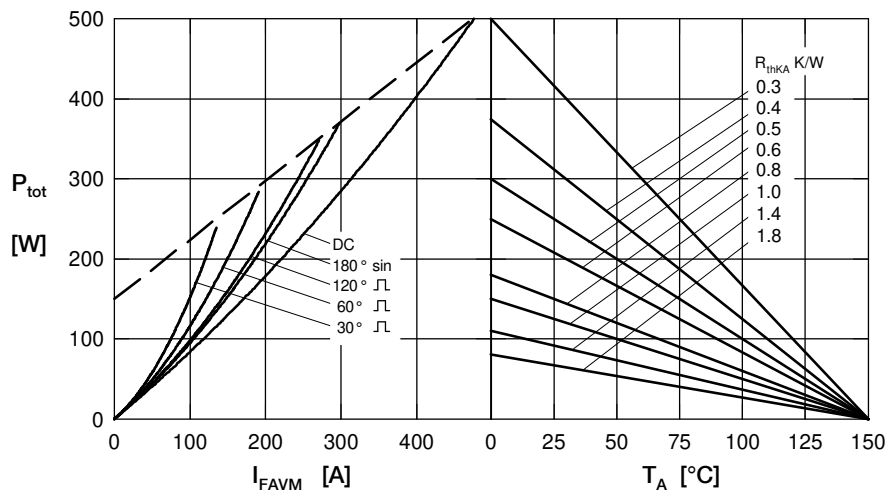


Fig. 4 Power dissipation versus forward current and ambient temperature (per diode)

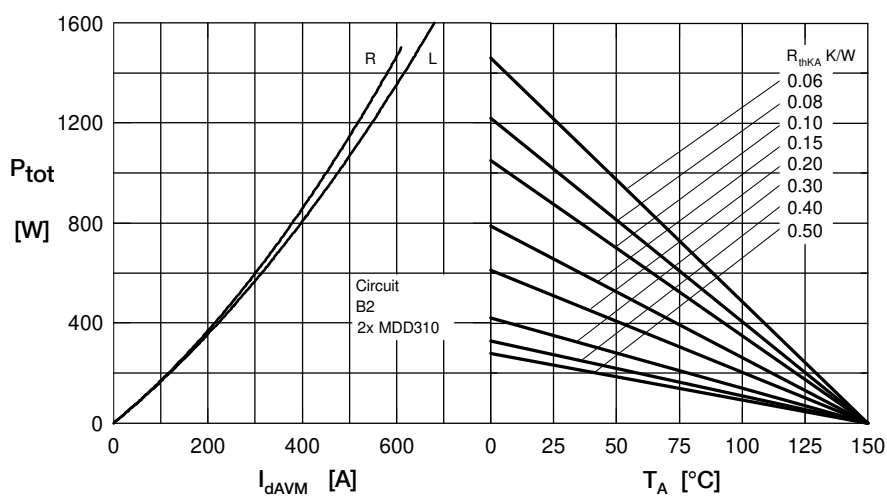


Fig. 5 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature R = resistive load, L = inductive load

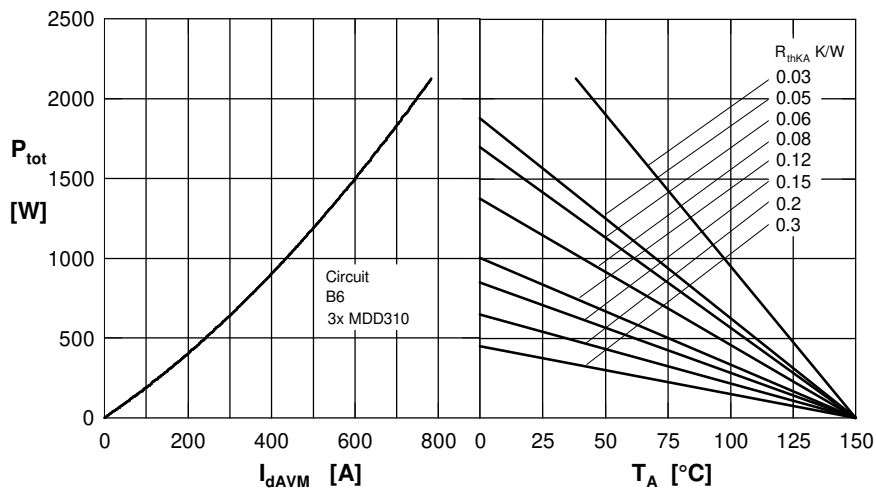
Rectifier


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

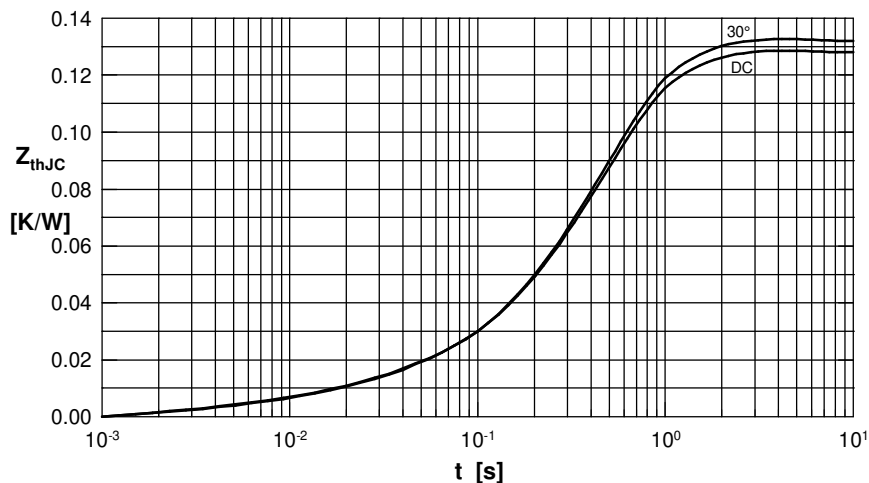


Fig. 7 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d .

d	R_{thJC} [K/W]
DC	0.129
180°	0.131
120°	0.132
60°	0.132
30°	0.133

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560

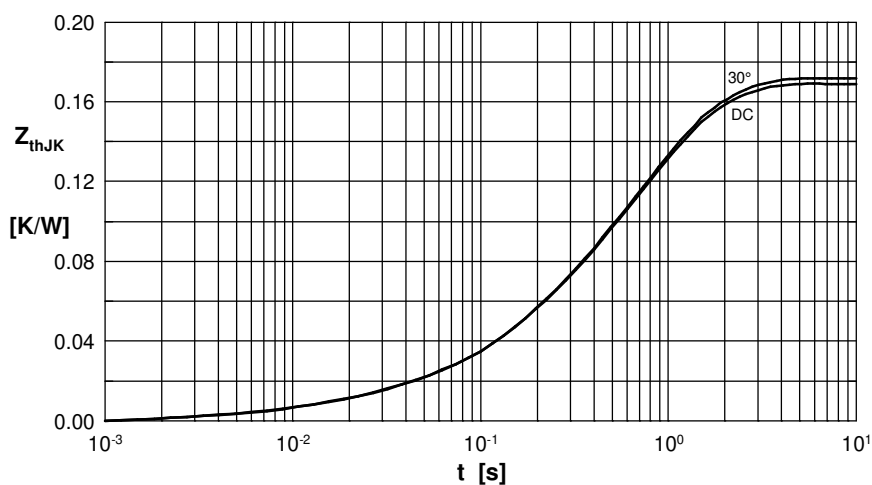


Fig. 8 Transient thermal impedance junction to heatsink (per diode)

R_{thJK} for various conduction angles d .

d	R_{thJK} [K/W]
DC	0.169
180°	0.171
120°	0.172
60°	0.172
30°	0.173

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560
4	0.0400	1.3600